Seoung-Hwan Park

List of Publications by Year
in descending order

176 papers	3,637 citations	257450 24 h-index	138484 58 g-index
178 all docs	178 docs citations	178 times ranked	3699 citing authors

#	Article	IF	Citations
1	Temperature Droop Characteristics of Internal Efficiency in <inline-formula> <tex-math notation="TeX">$hbox{In}_{x}hbox{Ga}_{1-x}hbox{N/GaN}$</tex-math></inline-formula> Quantum Well Light-Emitting Diodes. IEEE Photonics Journal, 2014, 6, 1-9.	2.0	1,139
2	Crystal-orientation effects on the piezoelectric field and electronic properties of strained wurtzite semiconductors. Physical Review B, 1999, 59, 4725-4737.	3.2	286
3	Comparison of zinc-blende and wurtzite GaN semiconductors with spontaneous polarization and piezoelectric field effects. Journal of Applied Physics, 2000, 87, 353-364.	2.5	203
4	Piezoelectric effects on electrical and optical properties of wurtzite GaN/AlGaN quantum well lasers. Applied Physics Letters, 1998, 72, 3103-3105.	3.3	173
5	Spontaneous polarization effects in wurtzite GaN/AlGaN quantum wells and comparison with experiment. Applied Physics Letters, 2000, 76, 1981-1983.	3.3	141
6	Crystal orientation effects on electronic properties of wurtzite InGaN/GaN quantum wells. Journal of Applied Physics, 2002, 91, 9904.	2.5	119
7	Electronic and Optical Properties of ${m a}$- and ${m m}$-Plane Wurtzite InGaNâ€“GaN Quantum Wells. IEEE Journal of Quantum Electronics, 2007, 43, 1175-1182.	1.9	117
8	Spontaneous and piezoelectric polarization effects in wurtzite ZnOâˆ•MgZnO quantum well lasers. Applied Physics Letters, 2005, 87, 253509.	3.3	100
9	Optical gain of strained GaAsSb/GaAs quantum-well lasers: A self-consistent approach. Journal of Applied Physics, 2000, 88, 5554-5561.	2.5	84
10	High-efficiency staggered 530 nm InGaN/InGaN/GaN quantum-well light-emitting diodes. Applied Physics Letters, 2009, 94, .	3.3	84
11	Dip-shaped InGaN/GaN quantum-well light-emitting diodes with high efficiency. Applied Physics Letters, 2009, 95, 063507.	3.3	64
12	Many-body optical gain of wurtzite GaN-based quantum-well lasers and comparison with experiment. Applied Physics Letters, 1998, 72, 287-289.	3.3	50
13	Crystal Orientation Effects on Electronic Properties of Wurtzite GaN/AlGaN Quantum Wells with Spontaneous and Piezoelectric Polarization. Japanese Journal of Applied Physics, 2000, 39, 3478-3482.	1.5	45
14	Cuprous halides semiconductors as a new means for highly efficient light-emitting diodes. Scientific Reports, 2016, 6, 20718.	3.3	37
15	Light emission enhancement in blue InGaAlN/InGaN quantum well structures. Applied Physics Letters, 2011, 99, .	3.3	35
16	Spontaneous emission rate of green strainâ€compensated InGaN/InGaN LEDs using InGaN substrate. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 195-198.	1.8	35
17	Crystal Orientation Effects on Many-Body Optical Gain of Wurtzite InGaN/GaN Quantum Well Lasers. Japanese Journal of Applied Physics, 2003, 42, L170-L172.	1.5	34
18	Optical and microstructural studies of atomically flat ultrathin In-rich InGaNâˆ•GaN multiple quantum wells. Journal of Applied Physics, 2008, 103, 063509.	2.5	29

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19	Optical gain improvement in type-II InGaN/GaNSb/GaN quantum well structures composed of InGaN/and GaNSb layers. Applied Physics Letters, 2010, 96, 051106.	3.3	29
20	Carrier density dependence of polarization switching characteristics of light emission in deep-ultraviolet AlGaN/AlN quantum well structures. Applied Physics Letters, 2013, 102, .	3.3	29
21	Heat treatment effects on electrical and optical properties of ternary compound In2O3â€"ZnO films. Journal of Applied Physics, 2002, 92, 5761-5765.	2.5	27
22	Optical gain in InGaNâˆ•InGaAlN quantum well structures with zero internal field. Applied Physics Letters, 2008, 92, 171115.	3.3	26
23	Many-body effects on optical gain in strained hexagonal and cubic GaN/AlGaN quantum well lasers. Applied Physics Letters, 1997, 71, 398-400.	3.3	25
24	Optical properties of type-II InGaN/GaAsN/GaN quantum wells. Optical and Quantum Electronics, 2009, 41, 779-785.	3.3	25
25	Piezoelectric effects on many-body optical gain of zinc-blende and wurtzite GaN/AlGaN quantum-well lasers. Applied Physics Letters, 1999, 75, 1354-1356.	3.3	24
26	Effects of Oxygen Concentration on Characteristics of RF-Sputtered In2O3â€"ZnO Thin Films. Japanese Journal of Applied Physics, 2001, 40, 1429-1430.	1.5	24
27	Finite element analysis of valence band structures in quantum wires. Journal of Applied Physics, 2004, 96, 2055-2062.	2.5	22
28	Many-body optical gain of GaInNAsâˆ•GaAs strained quantum-well lasers. Applied Physics Letters, 2004, 85, 890-892.	3.3	21
29	EXTENDED TANH-METHODS AND SOLITONIC SOLUTIONS OF THE GENERAL SHALLOW WATER WAVE MODELS. International Journal of Modern Physics C, 2004, 15, 363-370.	1.7	21
30	Numerical Analysis of Multilayer Organic Light-Emitting Diodes. Journal of Lightwave Technology, 2007, 25, 2828-2836.	4.6	20
31	Electronic and optical properties of staggered InGaN/InGaN quantumâ€well lightâ€emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2637-2640.	1.8	20
32	Optical gain characteristics of non-polar Al-rich AlGaN/AlN quantum well structures. Journal of Applied Physics, 2011, 110, 063105.	2.5	20
33	Strain and piezoelectric potential effects on optical properties in CdSe/CdS core/shell quantum dots. Journal of Applied Physics, 2011, 109, .	2.5	18
34	High-efficiency BAlGaN/AlN quantum well structures for optoelectronic applications in ultraviolet spectral region. Optics Express, 2015, 23, 3623.	3.4	18
35	Crystal orientation effects on electronic and optical properties of wurtzite ZnO/MgZnO quantum well lasers. Optical and Quantum Electronics, 2007, 38, 935-952.	3.3	17
36	Internal field engineering in CdZnO/MgZnO quantum well structures. Applied Physics Letters, 2009, 94, .	3.3	16

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37	Optical Gain in GaN Quantum Well Lasers with Quaternary AlInGaN Barriers. Japanese Journal of Applied Physics, 2005, 44, 7460-7463.	1.5	15
38	Piezoelectric and Spontaneous Polarization Effects on Many-Body Optical Gain of Wurtzite InGaN/GaN Quantum Well with Arbitrary Crystal Orientation. Japanese Journal of Applied Physics, 2003, 42, 5052-5055.	1.5	13
39	Internal field effects on electronic and optical properties of ZnO/BeZnO quantum well structures. Physica B: Condensed Matter, 2014, 441, 12-16.	2.7	13
40	On the Theory of Optical Gain of Strained-Layer Hexagonal and Cubic GaN Quantum-Well Lasers. Japanese Journal of Applied Physics, 1996, 35, 6079-6083.	1.5	11
41	Effect of (101Ì„0) crystal orientation on many-body optical gain of wurtzite InGaN/GaN quantum well. Journal of Applied Physics, 2003, 93, 9665-9668.	2.5	11
42	Highly polarized photoluminescence from c-plane InGaN/GaN multiple quantum wells on stripe-shaped cavity-engineered sapphire substrate. Scientific Reports, 2019, 9, 8282.	3.3	11
43	Spontaneous Polarization and Piezoelectric Effects on Inter-Subband Scattering Rate in Wurtzite GaN/AlGaN Quantum-Well. Japanese Journal of Applied Physics, 2001, 40, L941-L944.	1.5	10
44	Comparison of light emission in InGaN/GaN light-emitting diodes with graded, triangular, and parabolic quantum-well structures. Journal of the Korean Physical Society, 2012, 60, 505-508.	0.7	10
45	Temperature characteristics of spontaneous emission and optical gain in blue InGaN/GaN quantum well structures. Journal of Applied Physics, 2013, 114, .	2.5	10
46	Quantum efficiency affected by localized carrier distribution near the V-defect in GaN based quantum well. Applied Physics Letters, 2013, 103, .	3.3	10
47	Theoretical Studies on TM-Polarized Light Emission for Ultraviolet BAlGaN/AlN Optoelectronic Devices. IEEE Photonics Technology Letters, 2016, 28, 2153-2155.	2.5	10
48	Piezoelectric and spontaneous polarization effects on exciton binding energy and light emission properties of wurtzite ZnO/MgO quantum dots. Solid State Communications, 2017, 261, 21-25.	1.9	10
49	Screening Effects on Electron-Longitudinal Optical-Phonon Intersubband Scattering in Wide Quantum Well and Comparison with Experiment. Japanese Journal of Applied Physics, 2000, 39, 6601-6605.	1.5	9
50	Intersubband transition in lattice-matched BGaN/AlN quantum well structures with high absorption coefficients. Optics Express, 2017, 25, 3143.	3.4	9
51	Many-body optical gain of (101Ì„0) wurtzite GaN/AlGaN quantum-well lasers. Applied Physics Letters, 2000, 77, 4095-4097.	3.3	8
52	Intraband relaxation time in wurtzite InGaN/GaN quantum-well structures with (101Ì„0) crystal orientation. Applied Physics Letters, 2002, 80, 2830-2832.	3.3	8
53	High optical polarization ratio of semipolar (202Â¯1Â¯)-oriented InGaN/GaN quantum wells and comparison with experiment. Journal of Applied Physics, 2012, 112, .	2.5	8
54	High-efficiency InGaN/GaN light-emitting diodes with electron injector. Semiconductor Science and Technology, 2012, 27, 115003.	2.0	8

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55	Polarization characteristics of semipolar (112Ì„2) InGaN/GaN quantum well structures grown on relaxed InGaN buffer layers and comparison with experiment. Optics Express, 2014, 22, 14850.	3.4	8
56	Optical Properties of Strained CdZnTe/ZnTe Quantum Dots. Journal of the Korean Physical Society, 2009, 55, 2517-2521.	0.7	8
57	Al Composition Dependence of the Optical Gain Characteristics of a-plane Al-rich AlGaN/AlN Quantum-well Structures. Journal of the Korean Physical Society, 2011, 59, 357-361.	0.7	8
58	Theoretical investigation of gain and linewidth enhancement factor for 1.55-Î¼m tensile strained quantum-well lasers. Journal of Lightwave Technology, 1997, 15, 711-716.	4.6	7
59	Reduction of as carryover by PH3 overpressure in metalorganic vapor-phase epitaxy. Journal of Crystal Growth, 1997, 179, 26-31.	1.5	7
60	Electronic Properties of InGaAs/GaAs Strained Coupled Quantum Dots Modeled by Eight-Bandk Â·pTheory. Japanese Journal of Applied Physics, 2003, 42, 144-149.	1.5	7
61	Exciton Binding Energies in Zincblende GaN/AlGaN Quantum Wells. Japanese Journal of Applied Physics, 2004, 43, 140-143.	1.5	7
62	Mole Fraction Effect on the Interband Transition Energy of CdTe/Cd$_{x}$Zn$_{1-x}$TeNanostructures. Journal of the Korean Physical Society, 2010, 57, 178-182.	0.7	7
63	Intraband Relaxation Time in Wurtzite GaN/InAlN Quantum-Well. Japanese Journal of Applied Physics, 1999, 38, L815-L818.	1.5	6
64	Crystal orientation dependence of many-body optical gain in wurtzite GaN/AlGaN quantum-well lasers. Semiconductor Science and Technology, 2002, 17, 686-691.	2.0	6
65	Intraband relaxation time in InGaNAs quantum-well lasers and comparison with experiment. Physica Status Solidi (B): Basic Research, 2005, 242, 1022-1026.	1.5	6
66	Spontaneous emission and optical gain characteristics of blue InGaAlN/InGaN quantum well structures with reduced internal field. Journal of Applied Physics, 2012, 112, 043107.	2.5	6
67	Partial strain relaxation effects on polarization anisotropy of semipolar (112Â¯2) InGaN/GaN quantum well structures. Applied Physics Letters, 2013, 103, 221108.	3.3	6
68	Strong and robust polarization anisotropy of site- and size-controlled single InGaN/GaN quantum wires. Scientific Reports, 2020, 10, 15371.	3.3	6
69	High Temperature Characteristics of Strained InGaAs/InGaAlAs Quantum Well Lasers. Japanese Journal of Applied Physics, 1997, 36, 3528-3530.	1.5	5
70	Non-Markovian gain and luminescence of an InGaN-AlInGaN quantum-well with many-body effects. IEEE Journal of Quantum Electronics, 2005, 41, 1253-1259.	1.9	5
71	Theoretical studies on the two-dimensional electron-gas properties of MgZnO/MgO/ZnO heterostructures. Journal of the Korean Physical Society, 2016, 69, 96-98.	0.7	5
72	Effects of Modulation Doping on the Optical Properties of a Type-II 1.55-mum GaAsSb/InGaNAs/GaAs Trilayer Quantum-Well Structure. Journal of the Korean Physical Society, 2010, 57, 826-828.	0.7	5

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73	Bandgap Effects of Quantum Well Active-Layer on Threshold Current Density, Differential Gain and Temperature Characteristics of 1.3 Âµm InGaAlAs/InP Quantum Well Lasers. Japanese Journal of Applied Physics, 2002, 41, 1354-1358.	1.5	4
74	Optical anisotropy in nonpolar (101Ì„0)-oriented m-plane GaN/AlGaN quantum wells and comparison with experiment. Applied Physics A: Materials Science and Processing, 2008, 91, 361-364.	2.3	4
75	Strain relaxation effect on electronic properties of compressively strained InGaAs/InP vertically stacked multiple quantum wires. Journal of Applied Physics, 2010, 108, 023104.	2.5	4
76	Optical Emission Characteristics of Pseudopolarization-Matched Green AlInGaN/InGaN Quantum Well Structures. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1-8.	2.9	4
77	Effects of wetting layer on exciton binding energy of strained CdTe/ZnTe pyramidal quantum dots. Solid State Communications, 2015, 204, 61-63.	1.9	4
78	Effect of boron incorporation on light emission characteristics of UV BAlGaN/AlN quantum well structures. Applied Physics Express, 2016, 9, 021001.	2.4	4
79	Strain and built-in fields in wurtzite GaN/Al In1â^’xN quantum wells and quantum dots. Superlattices and Microstructures, 2018, 120, 611-615.	3.1	4
80	Control of the 3-Fold Symmetric Shape of Group III-Nitride Quantum Dots: Suppression of Fine-Structure Splitting. Nano Letters, 2020, 20, 8461-8468.	9.1	4
81	Optical Gain Characteristics in 1.55-m GaAsSbN/GaAs Quantum Well Structures. Journal of the Korean Physical Society, 2007, 50, 1152.	0.7	4
82	Optical Gain in Wurtzite ZnO/ZnMgO Quantum Well Lasers. Japanese Journal of Applied Physics, 2005, 44, L1403-L1406.	1.5	3
83	Electronic and optical properties of 530 nm strain-compensated hybrid InGaN/InGaN/ZnO quantum well light-emitting diodes. Journal of Applied Physics, 2008, 104, 036106.	2.5	3
84	Intersubband nonlinear optical rectification in CdTe/Zn x Cd1â^’x Te/ZnTe asymmetric rectangular quantum wells. Journal of the Korean Physical Society, 2012, 61, 1080-1082.	0.7	3
85	Structural effects on the electronic properties of vertically-coupled CdTe/ZnTe quantum-dot molecules. Journal of the Korean Physical Society, 2012, 61, 2036-2041.	0.7	3
86	Characteristics of built-in polarization potentials in vertically and laterally arranged InGaN/GaN quantum dots. Journal of Applied Physics, 2012, 112, .	2.5	3
87	Optical polarization characteristics of m-plane InGaN/GaN quantum well structures and comparison with experiment. Applied Physics Letters, 2013, 103, 101107.	3.3	3
88	Hybrid InGaN/CdZnO quantum well structures for optoelectronic applications in the short wavelength spectral region. Physica Status Solidi (B): Basic Research, 2013, 250, 378-381.	1.5	3
89	Theoretical study of a two-dimensional electron gas in wurtzite ZnO/MgZnO heterostructures and comparison with experiment. Journal of the Korean Physical Society, 2015, 67, 1844-1847.	0.7	3
90	Effects of AlGaN delta-layer insertion on light emission characteristics of ultraviolet AlGaN/AlN quantum well structures. Physica Status Solidi (B): Basic Research, 2015, 252, 1844-1847.	1.5	3

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91	Quaternary AlInGaN/InGaN quantum well on vicinal c-plane substrate for high emission intensity of green wavelengths. Journal of Applied Physics, 2015, 117, 185707.	2.5	3
92	Polarization characteristics of 480â€“680 nm (1 1<mml:math) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 722 Td (xmlns:mml="http://www.w InGaN/GaN quantum well structures with strain relaxation effects. Superlattices and Microstructures, 2015, 86, 531-535.	3.1	3
93	Theoretical studies on light emission characteristics of high-efficiency BInGaN/GaN quantum well structures with blue spectral range. Superlattices and Microstructures, 2016, 96, 150-154.	3.1	3
94	Intersubband absorption coefficients of GaN/AlN and strain-compensated InGaN/InAlN quantum well structures. Superlattices and Microstructures, 2016, 100, 508-513.	3.1	3
95	Effects of a delta-layer insertion on the ultraviolet light emission characteristics of III-nitride quantum well structures. Superlattices and Microstructures, 2017, 112, 665-670.	3.1	3
96	Intersubband absorption of p-type wurtzite GaN/AlN quantum well for fiber-optics telecommunication. Journal of Applied Physics, 2017, 122, 184303.	2.5	3
97	Lattice-matched double dip-shaped BAlGaN/AlN quantum well structures for ultraviolet light emission devices. Superlattices and Microstructures, 2018, 117, 413-417.	3.1	3
98	Substrate dependence of TM-polarized light emission characteristics of BAlGaN/AlN quantum wells. Optics Communications, 2018, 417, 76-78.	2.1	3
99	Simulation studies on guard ring effects on edge breakdown suppression of InGaAs/InP avalanche photodiodes. Japanese Journal of Applied Physics, 2018, 57, 106506.	1.5	3
100	Anisotropic strain effects on light emission characteristics of CdZnO/ZnO quantum well structures. Physics Letters, Section A: General, Atomic and Solid State Physics, 2019, 383, 125995.	2.1	3
101	A broadband ultraviolet light source using GaN quantum dots formed on hexagonal truncated pyramid structures. Nanoscale Advances, 2020, 2, 1449-1455.	4.6	3
102	Optical anisotropy in type-II (110)-oriented GaAsSb/GaAs quantum wells. Solid State Communications, 2020, 314-315, 113934.	1.9	3
103	Linewidth enhancement factor of hybrid green InGaN/MgZnO quantum well structures. Physica E: Low-Dimensional Systems and Nanostructures, 2021, 130, 114678.	2.7	3
104	Intraband Relaxation Time in Short-wavelength II-VI CdZnSe/ZnSeQuantum-well Structures. Journal of the Korean Physical Society, 2009, 55, 671-674.	0.7	3
105	High temperature characteristics of strained InGaAs/InGaAsP quantum well lasers lattice matched to GaAs. IEEE Photonics Technology Letters, 1994, 6, 1297-1299.	2.5	2
106	Structural Dependence of Electronic Properties in (10ar10) Wurtzite GaN/AlGaN Quantum Wells. Japanese Journal of Applied Physics, 2002, 41, 2084-2089.	1.5	2
107	Spontaneous and piezoelectric polarization effects on linewidth enhancement factor of wurtzite InGaN/GaN quantum-well lasers. Physica Status Solidi A, 2003, 198, 336-342.	1.7	2
108	Enhancement of optical gain in Li:CdZnO/ZnMgO quantum well lasers. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2652-2654.	2.7	2

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109	Enhancement of light power for strain-compensated hybrid InGaN/InGaN/MgZnO light-emitting diodes. Applied Physics Letters, 2010, 97, 121107.	3.3	2
110	Effects of polarization field on vertical transport in GaN/AlGaN resonant tunneling diodes. Journal of the Korean Physical Society, 2012, 60, 1957-1960.	0.7	2
111	Strain effects on the optical properties of compressively-strained InGaAs/InP multiple quantum wires. Journal of the Korean Physical Society, 2014, 64, 1196-1201.	0.7	2
112	Optical Gain Characteristics in GaAsPN/GaPN Quantum Well Lasers for Silicon Integration. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 153-159.	2.9	2
113	Confinement-dependent exciton binding energy in wurtzite GaN/Al In1â˘'N quantum dots. Superlattices and Microstructures, 2017, 109, 254-258.	3.1	2
114	Dip-Shaped AlGaN/AlN Light-Emitting Diodes With Delta-Layer Containing Boron. IEEE Photonics Technology Letters, 2017, 29, 1042-1045.	2.5	2
115	Properties of the Two-Dimensional Electron-Gas of a Hybrid MgZnO/InGaN/ZnO Heterostructure with an InGaN Channel Layer. Journal of the Korean Physical Society, 2019, 75, 326-330.	0.7	2
116	Theoretical study of optical properties of non-polar BAlGaN/AlN quantum wells lattice-matched to AlN. Solid State Communications, 2019, 290, 67-69.	1.9	2
117	Comparison of optical properties of polarization-matched c-plane and lattice-matched a-plane BInGaN/GaN quantum well structures. Physica B: Condensed Matter, 2019, 570, 94-99.	2.7	2
118	Strain and built-in potential effects on optical properties of wurtzite GaN/AlInN quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2019, 108, 112-115.	2.7	2
119	Threshold Current Density of 1.3-m GaAsSb/GaInAs/GaAs Type-II Trilayer Quantum Well Lasers on GaAs Substrates. Journal of the Korean Physical Society, 2007, 50, 1018.	0.7	2
120	Crystal Orientation Dependence of Valence Band Structures in Zinc-Blende GaN/AlGaN Quantum Well Structures. Journal of the Korean Physical Society, 2007, 51, 605-611.	0.7	2
121	Many-Body Optical Gain in Zinc-Blende GaN/AlGaN Quantum Wells with (001), (111) and (110) Crystal Orientations. Journal of the Korean Physical Society, 2008, 52, 673-677.	0.7	2
122	Intraband Relaxation Time in Wurtzite GaN/AlGaN Quantum-Well Structures with Spontaneous Polarization Effects. Japanese Journal of Applied Physics, 2001, 40, 4570-4574.	1.5	1
123	Barrier-Width Effects on Electronic Properties of GaAsSb/GaAs Quantum Well Structures. Japanese Journal of Applied Physics, 2007, 46, 5025.	1.5	1
124	Structure parameters and external electric field effects on exciton binding energies of CdTe/ZnTe quantum dots. Journal of the Korean Physical Society, 2012, 60, 118-124.	0.7	1
125	Reduction in built-in polarization potentials in three vertically arranged InGaN/GaN quantum dots. Journal of the Korean Physical Society, 2013, 62, 809-812.	0.7	1
126	Ground-state switching characteristics in vertically-coupled InGaN/GaN quantum dots. Journal of the Korean Physical Society, 2013, 63, 2269-2272.	0.7	1

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127	Effects of depolarization on the electronic and the optical properties of InGaN/MgZnO quantum-well structures. Journal of the Korean Physical Society, 2014, 65, 1817-1819.	0.7	1
128	Light emission characteristics of blue strain-compensated InGaN/InGaN/InGaN light-emitting diodes. Journal of the Korean Physical Society, 2015, 66, 277-281.	0.7	1
129	Intersubband energies in strain-compensated InGaN/AlInN quantum well structures. AIP Advances, 2016, 6, 015014.	1.3	1
130	High-efficiency BGaN/AlN quantum wells for optoelectronic applications in ultraviolet spectral region. , 2017, , .		1
131	Capping layer thickness and quantum dot height dependences of strain and internal field distributions in wurtzite InGaN/GaN quantum dots. Superlattices and Microstructures, 2019, 128, 260-264.	3.1	1
132	Temperatureâ€Dependent Polarized Photoluminescence from câ€plane InGaN/GaN Multiple Quantum Wells Grown on Stripeâ€Shaped Cavityâ€Engineered Sapphire Substrate. Physica Status Solidi (B): Basic Research, 2020, 257, 1900526.	1.5	1
133	Cd content dependence of in-plane optical polarization in anisotropically strained c-plane CdZnO/ZnO quantum wells. Physica B: Condensed Matter, 2020, 596, 412393.	2.7	1
134	Non-Polar Wurtzite (1120) GaN/AlN Quantum Dots for Highly Efficient Opto-Electronic Devices. Electronics (Switzerland), 2020, 9, 1256.	3.1	1
135	Strain relaxation effects on TE-polarized light emission and in-plane polarization ratio in c-plane ultraviolet AlGaN/AlN quantum well structures. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 120, 114112.	2.7	1
136	Quantification of the effects of misfit strain on the energy states of zinc-blende spherical core/shell quantum dots. Journal of the Korean Physical Society, 2021, 79, 87-94.	0.7	1
137	Optical Properties of Green InGaN/GaN Quantum-Well Light-Emitting Diodes with Embedded AlGaN Â¥Ã Layer. Journal of the Korean Physical Society, 2009, 54, 226-230.	0.7	1
138	Electronic and Optical Properties of ZnO/ZnMgO Quantum Well Lasers with Piezoelectric and Spontaneous Polarizations. Journal of the Korean Physical Society, 2007, 50, 16-20.	0.7	1
139	Linewidth Enhancement Factor of Wurtzite (100)-Oriented InGaN/GaN Quantum-Well Lasers. Journal of the Korean Physical Society, 2007, 51, 2077.	0.7	1
140	Optical Gain of Type-II 1.55-Â¥Ã¬m GaAsSb/InGaNAs/GaAs Trilayer Quantum Wells. Journal of the Korean Physical Society, 2008, 53, 1886-1890.	0.7	1
141	Carrier screening effects on intersubband nonlinear optical rectification in wurtzite InGaN/GaN coupling quantum wells. Solid State Communications, 2022, 343, 114624.	1.9	1
142	Optical Gain Calculation for Strained Quantum Well Lasers by the Fourier Expansion Method. Japanese Journal of Applied Physics, 1996, 35, 5740-5744.	1.5	0
143	Negative Resistance of AlGaAs Diodes Co-doped with Si and Mn. Japanese Journal of Applied Physics, 1997, 36, L1481-L1482.	1.5	0
144	Many-body optical gain in ZnO- and GaN-based quantum well lasers. , 2006, , .		0

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145	Electronic and Optical Properties of 1.55 Âµm GaInNAs/GaAs Quantum-Well Structures. Japanese Journal of Applied Physics, 2007, 46, 152-155.	1.5	0
146	Optical Anisoptopy in $$left({11ar 22} ight)$$ -oriented InGaN/GaN quantum-well structures. Journal of the Korean Physical Society, 2012, 61, 803-806.	0.7	0
147	Large optical gain characteristics of tensile-strained 440-nm InGaN/AlInN quantum well structures. Journal of the Korean Physical Society, 2013, 63, 1815-1818.	0.7	0
148	Dip-shaped AlGaN/AlN quantum well structures with high TE-polarized optical gain. , 2013, , .		0
149	Crystal orientation effect on intersubband transition properties of (11n)-oriented ZnCdTe/ZnTe semiconductor quantum dots. Physica B: Condensed Matter, 2013, 420, 36-39.	2.7	0
150	Introduction to the Issue on Numerical Simulation of Optoelectronic Devices. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 0200602-0200602.	2.9	0
151	Interband transitions of AlN/Al x Ga1â[^]'x N (0.65 â‰ x â‰ 0.85) single quantum wells. Journal of the Korean Physical Society, 2014, 65, 1096-1100.	0.7	0
152	Effects of crystal orientation on the optical gain characteristics of blue AlInGaN/InGaN quantum-well structures. Journal of the Korean Physical Society, 2014, 65, 457-461.	0.7	0
153	Optical polarization anisoptopy in a-plane GaN/AlGaN quantum-well structures. Journal of the Korean Physical Society, 2014, 64, 1192-1195.	0.7	0
154	Optical polarization characteristics of m-plane GaN/AlGaN quantum well structures grown on m-plane SiC substrate. Solid State Communications, 2015, 223, 16-18.	1.9	0
155	Effects of spontaneous polarization on optical properties of ultraviolet BAlGaN/AlN quantum well structures. , 2016, , .		0
156	Optical gain characteristics of a-plane GaN/AlGaN quantum well lasers grown on strain-engineered MgZnO layer. Physica B: Condensed Matter, 2017, 521, 32-35.	2.7	0
157	Intersubband transition in p-type wurtzite GaN/AlGaN quantum well. , 2018, , .		0
158	P-type wurtzite GaN/AlGaN quantum well structures for normal incidence inter-subband photodetectors at 1.55 Âµm. Applied Physics Express, 2018, 11, 114001.	2.4	0
159	Effects of GaN capping layer on carrier occupation and interband transition probability of vertically coupled InGaN/GaN quantum dots. Physica B: Condensed Matter, 2020, 578, 411846.	2.7	0
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